

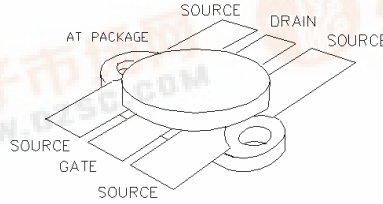


F1260

General Description

Silicon VDMOS and LDMOS transistors designed specifically for broadband RF applications. Suitable for Military Radios, Cellular and Paging Amplifier Base Stations, Broadcast FM/AM, MRI, Laser Driver and others.

"Polyfet"TM process features gold metal for greatly extended lifetime. Low output capacitance and high F_t enhance broadband performance



PATENTED GOLD METALIZED SILICON GATE ENHANCEMENT MODE RF POWER VDMOS TRANSISTOR

60Watts Single Ended

Package Style AT

HIGH EFFICIENCY, LINEAR, HIGH GAIN, LOW NOISE

ABSOLUTE MAXIMUM RATINGS (TC = 25 °C)

Total Device Dissipation	Junction to Case Thermal Resistance	Maximum Junction Temperature	Storage Temperature	DC Drain Current	Drain to Gate Voltage	Drain to Source Voltage	Gate to Source Voltage
150 Watts	1.2 °C/W	200 °C	-65 °C to 150 °C	8 A	50 V	50V	30V

RF CHARACTERISTICS (60WATTS OUTPUT)

SYMBOL	PARAMETER	MIN	TYP	MAX	UNITS	TEST CONDITIONS
Gps	Common Source Power Gain	10			dB	$I_{dq} = 1.6 \text{ A}, V_{ds} = 12.5 \text{ V}, F = 175 \text{ MHz}$
η	Drain Efficiency		60		%	$I_{dq} = 1.6 \text{ A}, V_{ds} = 12.5 \text{ V}, F = 175 \text{ MHz}$
VSWR	Load Mismatch Toleranc			20:1	Relative	$I_{dq} = 1.6 \text{ A}, V_{ds} = 12.5 \text{ V}, F = 175 \text{ MHz}$

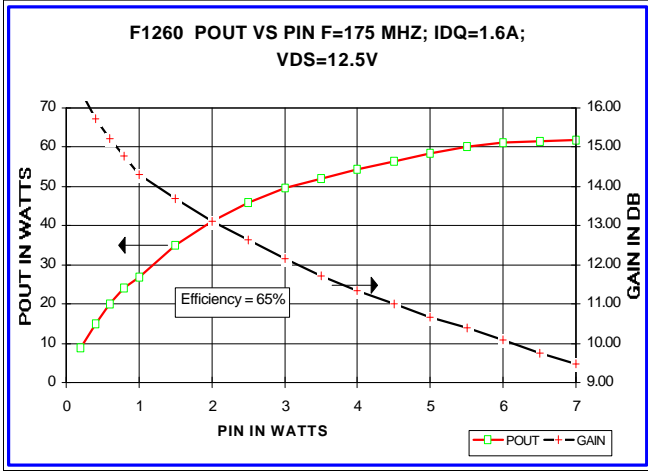
ELECTRICAL CHARACTERISTICS (EACH SIDE)

SYMBOL	PARAMETER	MIN	TYP	MAX	UNITS	TEST CONDITIONS
Bvdss	Drain Breakdown Voltag	40			V	$I_{ds} = 0.2 \text{ A}, V_{gs} = 0 \text{ V}$
Idss	Zero Bias Drain Curren			4	mA	$V_{ds} = 12.5 \text{ V}, V_{gs} = 0 \text{ V}$
Igss	Gate Leakage Curren			1	uA	$V_{ds} = 0 \text{ V}, V_{gs} = 30 \text{ V}$
Vgs	Gate Bias for Drain Curren	1		7	V	$I_{ds} = 0.4 \text{ A}, V_{gs} = V_{ds}$
gM	Forward Transconductanc		3.2		Mho	$V_{ds} = 10 \text{ V}, V_{gs} = 5 \text{ V}$
Rdson	Saturation Resistanc		0.25		Ohm	$V_{gs} = 20 \text{ V}, I_{ds} = 32 \text{ A}$
Idsat	Saturation Curren		30		Amp	$V_{gs} = 20 \text{ V}, V_{ds} = 10 \text{ V}$
Ciss	Common Source Input Capacitanc		160		pF	$V_{ds} = 12.5 \text{ V}, V_{gs} = 0 \text{ V}, F = 1 \text{ MHz}$
Crss	Common Source Feedback Capacitanc		24		pF	$V_{ds} = 12.5 \text{ V}, V_{gs} = 0 \text{ V}, F = 1 \text{ MHz}$
Coss	Common Source Output Capacitanc		120		pF	$V_{ds} = 12.5 \text{ V}, V_{gs} = 0 \text{ V}, F = 1 \text{ MHz}$

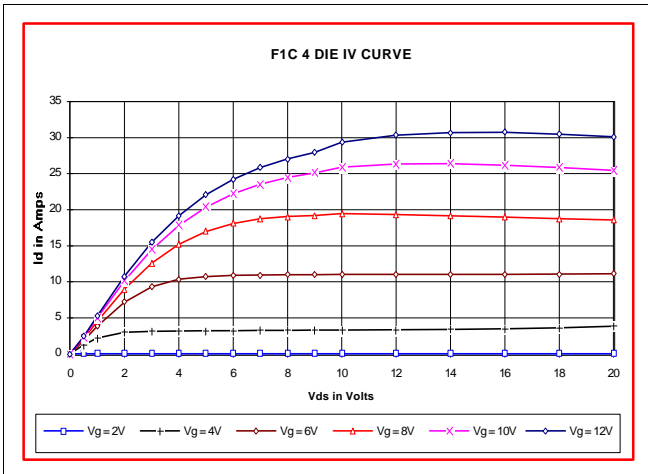


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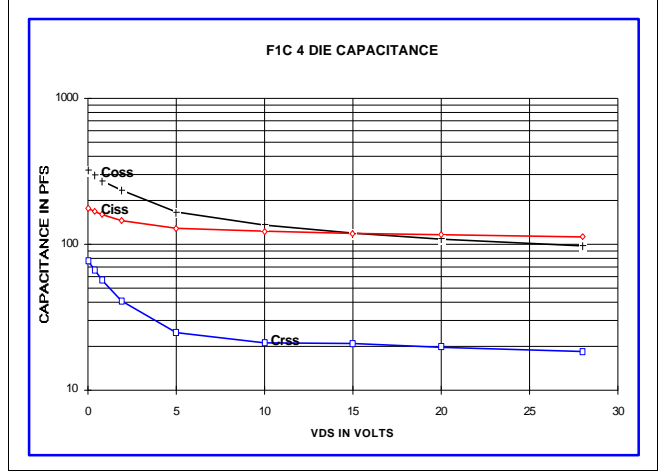
POUT VS PIN GRAPH



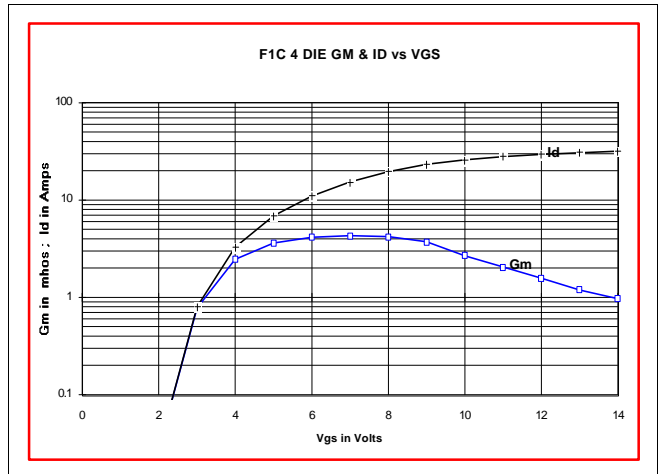
IV CURVE



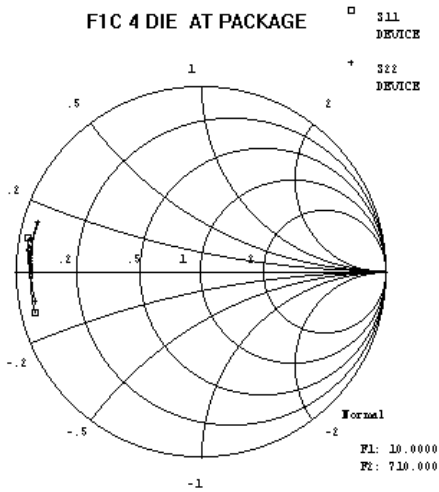
CAPACITANCE VS VOLTAGE



ID AND GM VS VGS



S11 AND S22 SMITH CHART



PACKAGE DIMENSIONS IN INCHES

